

74 (new). The memory cell, as set forth in claim 62, wherein the memory material comprises a chalcogenide material.

75 (new). The memory cell, as set forth in claim 62, wherein the memory material comprises a programmable resistive element.

76 (new). The memory cell, as set forth in claim 75, wherein the programmable resistive element changes between different resistance levels in response to electrical stimulus.

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#### REMARKS

Claims 2-31 have been canceled without prejudice. New claims 32-76 have been added. Consideration of the application as amended is respectfully requested.

If the Examiner believes that a telephonic interview will help speed this application toward issuance, Applicants invite the Examiner to contact the undersigned at (281) 970-4545.

[illegible]

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